

SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GA20SICP12-263.

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*      MODEL OF GeneSiC Semiconductor Inc.
*      $Revision: 2.0          $
*      $Date:      20-NOV-2015    $
*
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*
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GA20SICP12-263 SPICE Model
*
.SUBCKT GA20SICP12 DRAIN GATE SOURCE
Q1 DRAIN GATE SOURCE GA20SICP12_Q
D1 SOURCE DRAIN GA20SICP12_D1
D2 SOURCE DRAIN GA20SICP12_D2
*
.model GA20SICP12_Q NPN
+ IS      9.833E-48      ISE      1.073E-26      EG      3.23
+ BF      88            BR      0.55            IKF     5000
+ NF      1             NE      2              RB      3.09
+ IRB     0.006         RBM     0.101          RE      0.005
+ RC      0.035         CJC     910E-12         VJC     3.2509
+ MJC     0.51624       CJE     2.77e-9        VJE     2.896
+ MJE     0.472         XTI     3              XTB     -1.5
+ TRC1    8.500E-3      VCEO    1200          ICRATING 20
.MODEL GA20SICP12_D1 D
+ IS      5.48E-17      RS      0.03214547      N      1
+ IKF     1000          EG      1.2             XTI     3
+ CJO     1.15E-09     VJ      0.44           M      1.5
+ FC      0.5           TT      1.00E-10        IBV     1.00E-03
.MODEL GA20SICP12_D2 D
+ IS      1.54E-13      RS      0.23           N      3.941
+ IKF     19            EG      3.23           XTI     0
+ FC      0.5           TT      0              IBV     1.00E-03
.ENDS
*      End of GA20SICP12-263 SPICE Model

```